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	Application No.	Applicant(s)	
	09/973,277	WITVROUW ET AL.	
Notice of Allowability	Examin r	Art Unit	
	Pamela E Perkins	2822	
The MAILING DATE of this communication appeall claims being allowable, PROSECUTION ON THE MERITS IS therewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT Report the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in) or other appropriate communication is safety.	n this application. If not include unication will be mailed in due of	ed course. THIS
 This communication is responsive to the filing of the amend The allowed claim(s) is/are 1-23. The drawings filed on 09 October 2001 are accepted by th 	ne Examiner.		
 Acknowledgment is made of a claim for foreign priority under a)	nder 35 U.S.C. § 119(a)-(d)	or (†).	
 Certified copies of the priority documents have 			
Certified copies of the priority documents have	• •		
3. Copies of the certified copies of the priority do	cuments have been received	d in this national stage applicat	ion from the
International Bureau (PCT Rule 17.2(a)).			
* Certified copies not received: 5. Acknowledgment is made of a claim for domestic priority u reference was included in the first sentence of the specification.	ation or in an Application Da	ta Sheet. 37 CFR 1.78.	a specific
 (a) The translation of the foreign language provisional a Acknowledgment is made of a claim for domestic priority u in the first sentence of the specification or in an Application 	inder 35 U.S.C. §§ 120 and/		e was included
Applicant has THREE MONTHS FROM THE "MAILING DATE" or below. Failure to timely comply will result in ABANDONMENT of			
7. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give			OTICE OF
 CORRECTED DRAWINGS (as "replacement sheets") must (a) ☐ including changes required by the Notice of Draftspers 1) ☐ hereto or 2) ☐ to Paper No 		v (PTO-948) attached	
(b) ☐ including changes required by the proposed drawing of	correction filed, whic	h has been approved by the Ex	kaminer.
(c) ☐ including changes required by the attached Examiner	s Amendment / Comment or	in the Office action of Paper N	lo
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t			back) of
9. DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT FOR T			lote the
Attachment(s)			
1☐ Notice of References Cited (PTO-892)	5☐ Notice of Info	ormal Patent Application (PTO-	152)
2 Notice of Draftperson's Patent Drawing Review (PTO-948)		mmary (PTO-413), Paper No	·
3 Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No	^{3),} 7⊠ Examiner's A	mendment/Comment	
4 Examiner's Comment Regarding Requirement for Deposit of Biological Material	8⊠ Examiner's S 9∐ Other	Statement of Reasons for Allow	ance
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DETAILED ACTION

This office action is in response to the filing of the amendment on 5 January 2004. Claims 1-23 are pending.

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Paul Churilla on 22 January 2004.

The application has been amended as follows:

Claim 1 have been amended as follows:

1. A method for producing bulk micromachined devices for use in Microelectromechanical Systems (MEMS), comprising the steps of: providing a crystalline wafer with a front plane, processing from said wafer at least one bulk micromachined device comprising at least one elongated opening or cavity, the opening of cavity having a longitudinal axis, so that an angle is formed by said longitudinal axis and a line formed by intersection of the front plane of the wafer and a first cleavage plane, said first cleavage plane being defined as a plane along which a cleavage of the wafer is likely to occur, wherein said longitudinal axis is not

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paralleled with a second cleavage plane, said second cleavage plane also being defined as a plane along which cleavage is likely to occur.

Allowable Subject Matter

Claims 1-23 are allowed.

Reasons for Allowance

The following is an examiner's statement of reasons for allowance: prior art does not anticipate, teach, or suggest a method for producing bulk micromachined devices for use in Microeletromechanical Systems (MEMS) where a crystalline wafer comprising a front plane having at least one elongated opening or cavity, the opening or cavity having a longitudinal axis so that an angle is formed by the longitudinal axis and a line formed by an intersection of the front plane of the wafer and a first cleavage plane, wherein the longitudinal axis is not parallel with a second cleavage plane.

For example, Liang et al. (6,281,545) disclose a method of fabricating a flash memory device that comprises a split floating gate where a oxide layer is formed on a substrate, forming a patterned sacrificial layer on the oxide layer, implanting ions into the substrate to form source and drain regions comprising lightly doped source and drain regions with a channel region formed in-between the source and drain regions, forming spacers on the sidewalls of the sacrificial layer, forming a dielectric layer on the sacrificial layer and substrate and forming a control gate on the dielectric layer. Liang et al. further disclose etching the sacrificial layer to form two floating gates over the

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channel region, wherein the two floating gates are partially formed over the lightly doped source and drain regions. However, Liang et al. do not disclose, anticipate, teach, or suggest a method for producing bulk micromachined devices for use in Microeletromechanical Systems (MEMS) where a line is formed by an intersection of the front plane of the wafer and a first cleavage plane, wherein the longitudinal axis is not parallel with a second cleavage plane.

The prior art made of record in this action does not anticipate, teach, or suggest a method for producing bulk micromachined devices for use in Microeletromechanical Systems (MEMS) where a crystalline wafer comprising a front plane having at least one elongated opening or cavity, the opening or cavity having a longitudinal axis so that an angle is formed by the longitudinal axis and a line formed by an intersection of the front plane of the wafer and a first cleavage plane, wherein the longitudinal axis is not parallel with a second cleavage plane.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Pamela E Perkins whose telephone number is (571)

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272-1840. The examiner can normally be reached on Monday thru Friday, 9:00am to 5:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

PEP

